

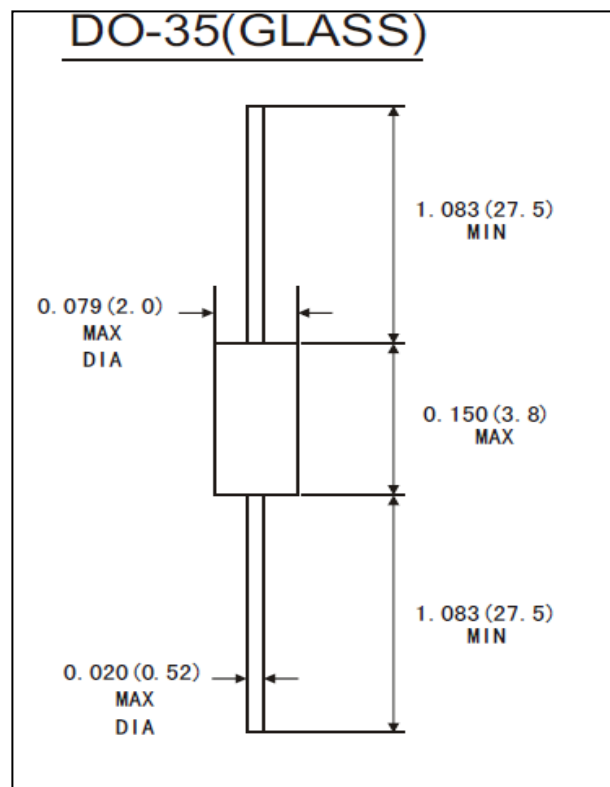


Silicon bidirectional diac

■ Mechanical data

- Case: DO-35 glass case
- Weight: Approx 0.13 gram

■ External and internal structure



■ Absolute Ratings

Symbols	Parameters		Value				Units
			DB3	DC34	DB4	DB6	
PC	Power Dissipation on printed Circuit(L=10mm)	TA=50°C	150				mW
ITRM	Repetitive Peak on-state Current	tp=10us f=100Hz	2.0	2.0	2.0	1.6	A
TSTG/TJ	Storage and Operating Junction Temperature		-40 to+125/-40 to +110				°C

■ Electrical Characteristics

Symbols	Parameters	Test Condition	Value				Units	
			DB3	DC34	DB4	DB6		
VBO	Break Voltage(Note 2)	C=22Nf(Note2) See diagram1	Min	28	30	35	56	V
			Typ	32	34	40	60	
			Max	36	38	45	70	
I+VBOI- I-VBOI	Breakover Voltage Symmetry	C=22Nf(Note2) See diagram1	Max	±3			±4	V
I±ΔVI	Dynamic Breakover Voltage(Note1)	ΔI=(IBO to IF=10Ma) See diagram1	Min	5			10	V
VO	Output Voltage (Note1)	See diagram2	Min	5			V	
IBO	Breakover Current (Note1)	C=22Nf(Note2)	Max	100			uA	
Tr	Rise Time(Note1)	See diagram3	Typ	1.5			uS	
IB	Leakage Current(Note1)	VB=0.5 VBO max See diagram1	Max	10			uA	

■ Characteristics(Typical)

DIAGRAM 1: Current-voltage characteristics

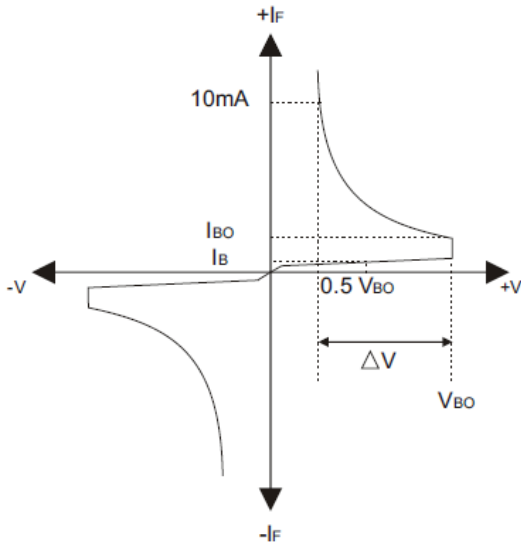


FIG.1-Power dissipation versus ambient temperature (maximum values)

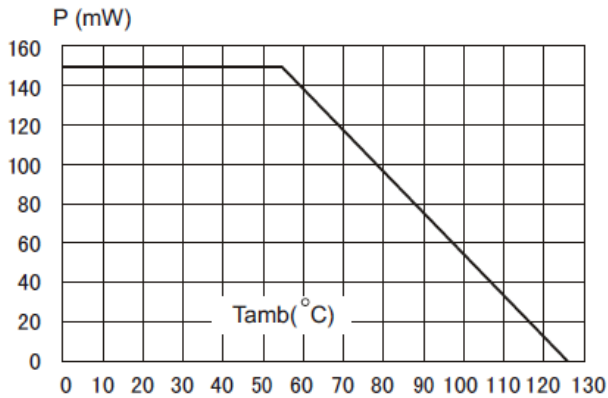


DIAGRAM 2: Test circuit for output voltage

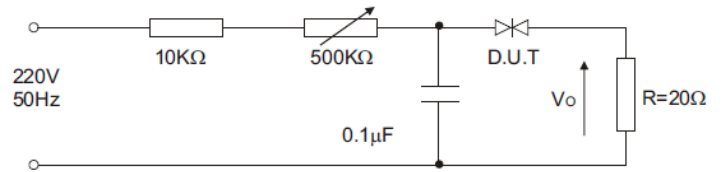


DIAGRAM 3: Test circuit see diagram2 adjust R for IP=0.5A

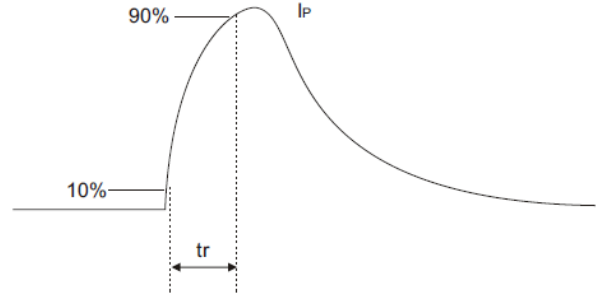


FIG.2-Relative variation of VBO versus junction temperature (typical values)

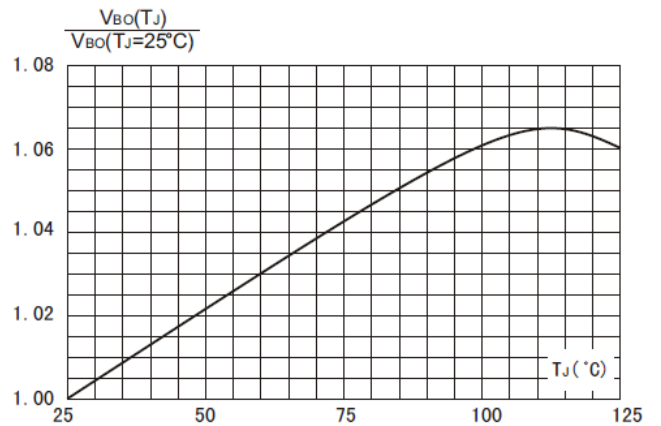


FIG.3-Peak pulse current versus pulse duration (maximum values)

